


MITSUBISHI IGBT  
**CY25AAJ-8F**

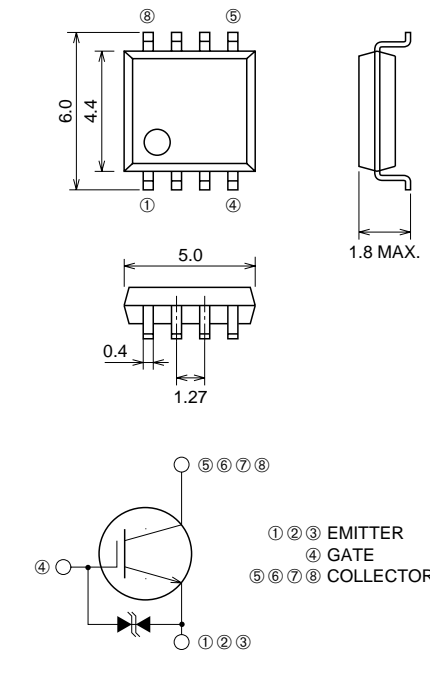
Nch IGBT for STROBE FLASHER

**CY25AAJ-8F**



- VCES ..... 400V
- ICM ..... 150A
- Drive voltage ..... 4V

**OUTLINE DRAWING** Dimensions in mm



**SOP-8**

**APPLICATION**

Strobe Flasher for camera

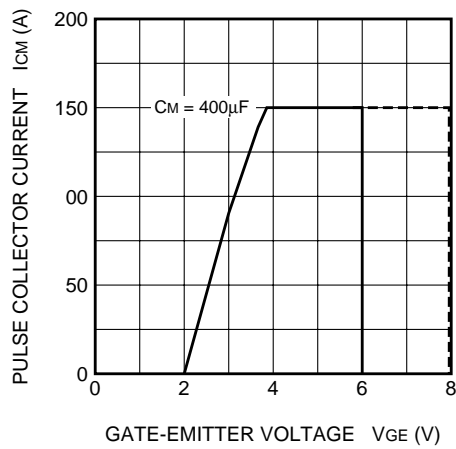
**MAXIMUM RATINGS** (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>CES</sub>	Collector-emitter voltage	V <sub>GE</sub> = 0V	400	V
V <sub>GES</sub>	Gate-emitter voltage	V <sub>CE</sub> = 0V	±6	V
V <sub>GEM</sub>	Peak gate-emitter voltage	V <sub>CE</sub> = 0V, t <sub>w</sub> = 10s	±8	V
I <sub>CM</sub>	Collector current (Pulsed)	C <sub>M</sub> = 400μF see figure1	150	A
T <sub>j</sub>	Junction temperature		-40 ~ +150	°C
T <sub>stg</sub>	Storage temperature		-40 ~ +150	°C

**ELECTRICAL CHARACTERISTICS** ( $T_j = 25^\circ\text{C}$ )

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) CES	Collector-emitter breakdown voltage	$I_C = 1\text{mA}, V_{GE} = 0\text{V}$	450	—	—	V
V (BR) GES	Gate-emitter breakdown voltage	$I_G = \pm 100\mu\text{A}, V_{CE} = 0\text{V}$	$\pm 8$	—	—	V
ICES	Collector-emitter leakage current	$V_{CE} = 400\text{V}, V_{GE} = 0\text{V}$	—	—	10	$\mu\text{A}$
IGES	Gate-emitter leakage current	$V_{GE} = \pm 6\text{V}, V_{CE} = 0\text{V}$	—	—	$\pm 10$	$\mu\text{A}$
VGE (th)	Gate-emitter threshold voltage	$V_{CE} = 10\text{V}, I_C = 1\text{mA}$	—	—	1.5	V

**Figure1. MAXIMUM PULSE COLLECTOR CURRENT**



**APPLICATION EXAMPLE**

